UNR92A0G

Silicon NPN epitaxial planar type

For digital circuits

■ Features

- Optimum for high-density mounting and downsizing of the equipment
- Contribute to low power consumption

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CBO}	50	V
Collector-emitter voltage (Base open)	V _{CEO}	50	V
Collector current	I_{C}	80	mA
Total power dissipation	P _T	125	mW
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55 to +125	\$°C 5

Package

- Code
- SSMini3-F3
- Pin Name
 - 1: Base
 - 2: Emitter
 - 3: Collector

■ Marking Symbol: KT

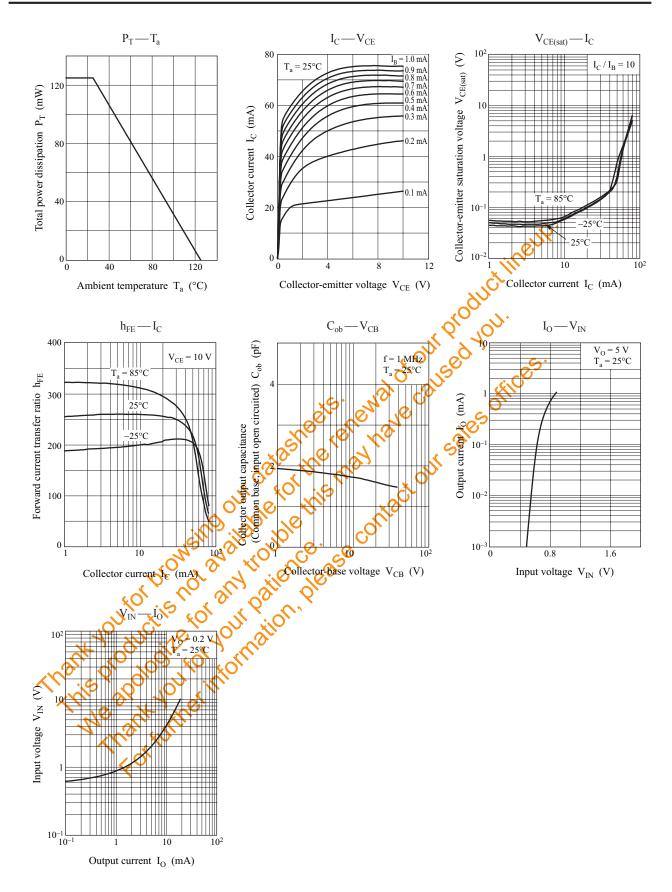


■ Electrical Characteristics

■ Absolute Maximum Ratings $T_a = 25$ °C				2: Emitter					
Parameter	Symbol	Rating	Unit 3: C	3: Collector					
Collector-base voltage (Emitter open)	V _{CBO}	50	V Ma	- ■ Marking Symbol: KT					
Collector-emitter voltage (Base open)	V _{CEO}	50	V	Walking Symbol. Ki					
Collector current	$I_{\rm C}$	80	mA Inte	emal Cor	nection				
Total power dissipation	P _T	125	mW CO	S. T.	R _D S.	C			
Junction temperature	T _j	125	°C O'C Alls	B⊶	WY -				
Storage temperature	T _{stg}	-55 to +125	12.00 NO	(0)		L⊸E			
■ Electrical Characteristics T _a = 2	2,C75/4 2,019/1/2	ouble of	V mA mW °C Conditions A, I _E = 0						
Parameter	Symbo	1	Conditions	Min	Тур	Max	Unit		
Collector-base voltage (Emitter open)	VCBO	$C = 10 \mu$	$A, I_E = 0$	50			V		
Collector-emitter-voltage (Base open)	() VCEO	$I_C = 2 \text{ mA}$	I_A , $I_B = 0$	50			V		
Collector-base cutoff current Emitter ope	en) Q _{CBO}	$V_{\rm CB} = 50$	$V, I_E = 0$			0.1	μΑ		
Collector-emitter cutoff current (Base op	en) I _{CEO}	$V_{\rm CE} = 50$	$V, I_{B} = 0$			0.5	μΑ		
Emitter-base cutoff current (Collector ope	en) I _{EBO}	$V_{\rm EB} = 6 V$	V , $I_C = 0$			0.01	mA		
Forward current transfer ratio	h _{FE}	$V_{CE} = 10$	$V, I_C = 5 \text{ mA}$	160		460			
Collector-emitter saturation Coltage	V _{CE(sat}	$I_C = 10 \text{ m}$	$A, I_B = 0.3 \text{ mA}$			0.25	V		
Output voltage high-level	V _{OH}	$V_{\rm CC} = 5 \text{ V}$	$V_{\rm A} = 0.5 \text{ V}, R_{\rm L} = 1 \text{ k}\Omega$	4.9			V		
Output voltage low-level	V _{OL}	$V_{\rm CC} = 5 \text{ V}$	$V_{\rm A}V_{\rm B} = 2.5 \text{ V}, R_{\rm L} = 1 \text{ k}\Omega$			0.2	V		
Input resistance	R_1			-30%	47	+30%	kΩ		
Transition frequency	f_T	$V_{\rm CB} = 10$	$V, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		150		MHz		

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

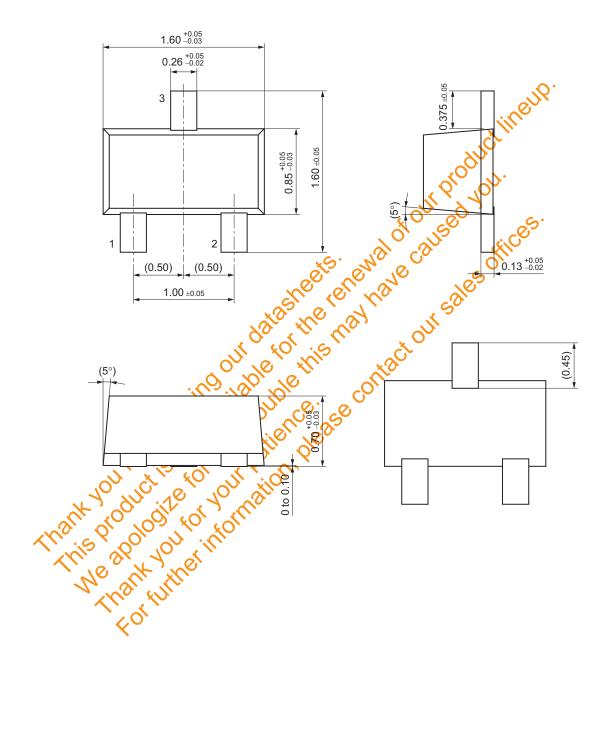
UNR92A0G Panasonic



2 SJH00242AED

Panasonic UNR92A0G

SSMini3-F3 Unit: mm



Request for your special attention and precautions in using the technical information and semiconductors described in this book

- (1) If any of the products or technical information described in this book is to be exported or provided to non-residents, the laws and regulations of the exporting country, especially, those with regard to security export control, must be observed.
- (2) The technical information described in this book is intended only to show the main characteristics and application circuit examples of the products, and no license is granted under any intellectual property right or other right owned by our company or any other company. Therefore, no responsibility is assumed by our company as to the infringement upon any such right owned by any other company which may arise as a result of the use of technical information described in this book.
- (3) The products described in this book are intended to be used for standard applications or general electronic equipment (such as office equipment, communications equipment, measuring instruments and household appliances). Consult our sales staff in advance for information on the following applications:
 - · Special applications (such as for airplanes, aerospace, automobiles, traffic control equipment, combustion equipment, life support systems and safety devices) in which exceptional quality and reliability are required, or if the failure or malfunction of the products may directly jeopardize life or harm the human body.
 - · Any applications other than the standard applications intended.
- (4) The products and product specifications described in this book are subject to change without notice to modification and/or improvement. At the final stage of your design, purchasing, or use of the products, therefore, ask for the most up-to-date Product Standards in advance to make sure that the latest specifications satisfy your requirements.
- (5) When designing your equipment, comply with the range of absolute maximum rating and the guaranteed operating conditions (operating power supply voltage and operating environment etc.). Especially, please be careful notion exceed the range of absolute maximum rating on the transient state, such as power-on, power-off and mode-switching. Otherwise, we will not be liable for any defect which may arise later in your equipment.
 - Even when the products are used within the guaranteed values, take into the consideration of incidence of break down and failure mode, possible to occur to semiconductor products. Measures on the systems such as redundant design, a resting the spread of fire or preventing glitch are recommended in order to prevent physical injury tife, social damages, for example, by using the products.
- (6) Comply with the instructions for use in order to prevent breakdown and characteristics change due to external factors (ESD, EOS, thermal stress and mechanical stress) at the time of handling, mounting of at customer's process. When using products for which damp-proof packing is required, satisfy the condition, such as shelf life and the elapsed time since first opening the packages.
- (7) This book may be not reprinted or reproduced whether wholls or partially, without the prior written permission of Matsushita Electric Industrial Co., Ltd.

aes, tak
aures on the
ent physical inju

prevent breakdown and
time of handling, thounting
ac conditions, such as shelf life and
reproduced whether wholly or partially